

FEATURES

- Drain Current : $I_D = 7.8A @ T_C = 25^\circ C$
- Drain Source Voltage
: $V_{DSS} = 800V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 1.2 \Omega (\text{Max}) @ V_{GS} = 10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

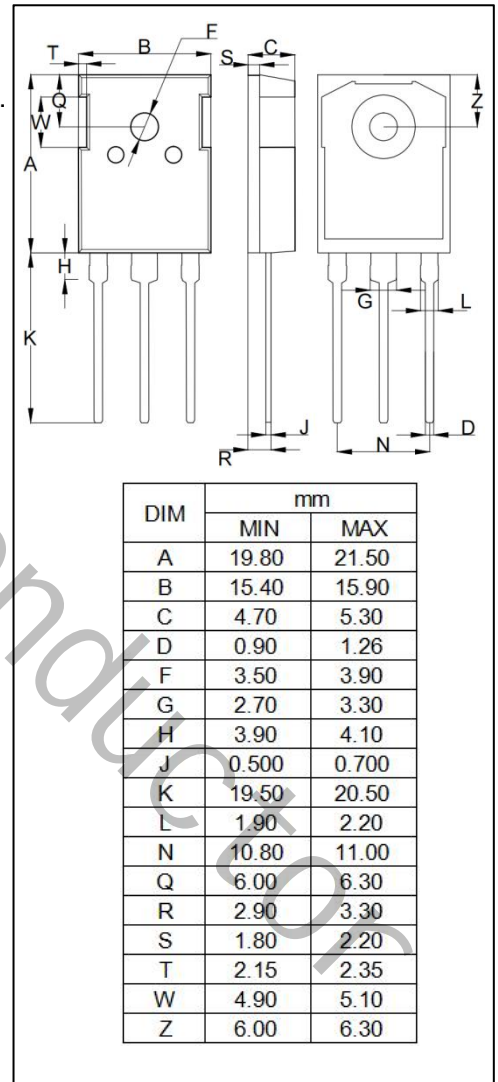
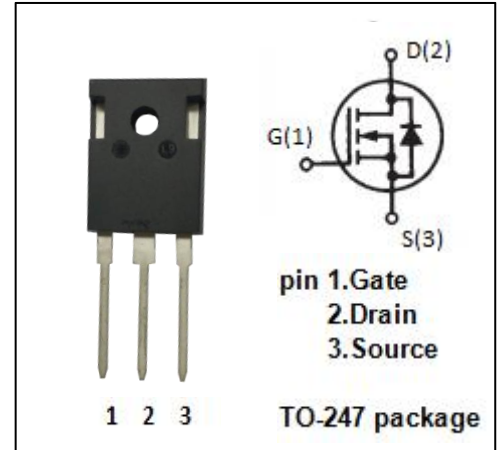
- Switching power supplies, converters, AC and DC motor controls.

• ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	7.8	A
I_{DM}	Drain Current-Single Plused	31	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	190	W
T_j	Max. Operating Junction Temperature	-55~150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.65	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	40	$^\circ C/W$



ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	800		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2	4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 4.7A		1.2	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800V; V _{GS} =0		100	uA
V _{SD}	Forward On-Voltage	I _S = 7.8A; V _{GS} =0		1.8	V

Semi conductor